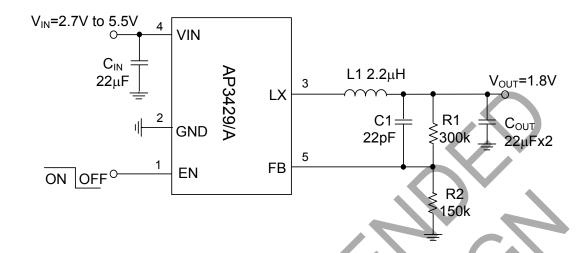


Typical Applications Circuit

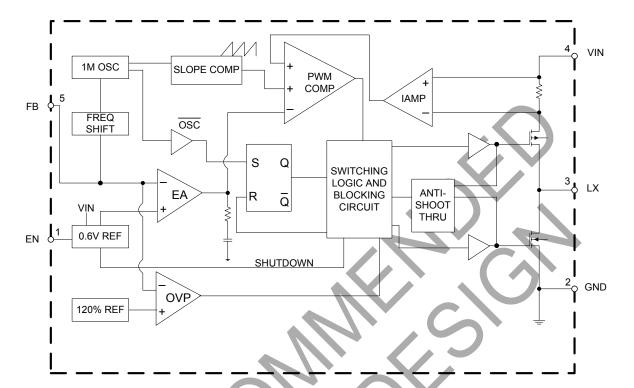


Pin Descriptions

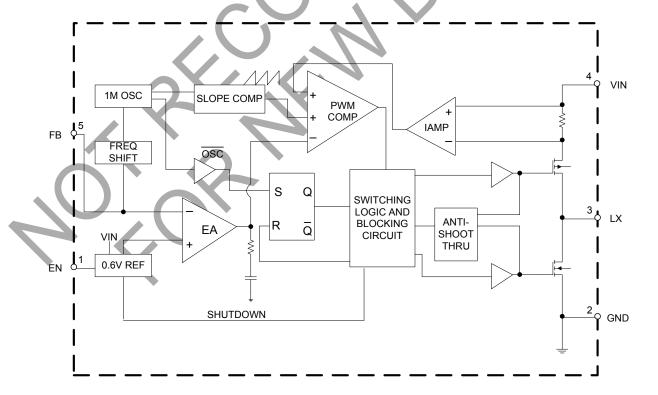
Pin Number	Pin Name	Function
1	EN	Enable control input. Force this pin voltage above 1.5V enables the chip, and below 0.4V shuts down the device.
2	GND	Ground pin.
3	LX	The drains of the internal main and synchronous power MOSFETs.
4	VIN	Bias supply. Chip main power supply pin.
5	FB	Feedback voltage to internal error amplifier. The threshold voltage is 0.6V.



Functional Block Diagram



Function Block Diagram of AP3429



Function Block Diagram of AP3429A



Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Rating	Unit
V _{IN}	Input Voltage	-0.3 to 6	V
V _{EN}	EN Pin Voltage	-0.3 to V _{IN} +0.3	
V_{LX}	LX Pin Voltage	-0.3 to V _{IN} +0.3	
V_{FB}	Feedback Pin Voltage	-0.3 to V _{IN} +0.3	V
P_{D}	Power Dissipation (on PCB, T _A = +25°C)	0.4	W
θJA	Thermal Resistance (Junction to Ambient)	220	°C/W
θις	Thermal Resistance (Junction to Case, Simulation)	130	°C/W
TJ	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature	-55 to +150	°C
V _{MM}	ESD (Machine Model)	200	V
V _{НВМ}	ESD (Human Body Model)	2000	V

Note 4: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{IN}	Input Voltage Range	2.7	5.5	V
T _A	Operating Ambient Temperature	-40	+85	°C
TJ	Junction Temperature Range	-40	+125	°C



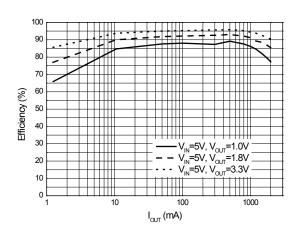
Electrical Characteristics (@ V_{IN} = 5V, V_{OUT} = 1.8V, L = 2.2 μ H, C_{IN} = 22 μ F, C_{OUT} = 22 μ F×2, T_A = +25°C, unless otherwise specified.)

Symbol	Parameters	Conditions	Min	Тур	Max	Unit
Vin	Input Voltage Range	_	2.7	1	5.5	٧
V_{FB}	Regulated Feedback Voltage	-	0.588	0.6	0.612	V
I _{FB}	FB Leakage Current	V _{FB} = 1V	_		0.2	μΑ
ΙQ	Quiescent Current	V _{FB} = 0.65V	_	90	_	μΑ
I _{SD}	Shutdown Current	V _{EN} = 0V	_	0.1	1	μΑ
I _{LIM}	Peak Inductor Current	-	3		_	Α
V _{SCP}	Short Circuit Protection Latch Off Threshold	-	-	0.3		V
fosc	Oscillator Frequency	-			-	MHz
	Drain to Source On-state Resistance	I _{LX} = 100mA, high side	_	110	-	mΩ
R _{DS(ON)}		I _{LX} = 100mA, low side	-	80	_	
V _{ENH}	EN High Threshold		1.5	1	_	V
V _{ENL}	EN Low Threshold	-	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	0.4	V
I _{EN}	EN Leakage Current	$V_{IN} = V_{EN} = 5V$	-1.0	ı	1.0	μΑ
V _{UVLO}	Input UVLO Threshold	-	_	2.4	2.7	V
V _{HYS}	UVLO Hysteresis		_	0.2	_	V
_	Maximum Duty Cycle	-	100	1	_	%
Rosch	Output Discharge Switch On Resistance		_	50	_	Ω
Тотр	Over Temperature Protection	-	-	+160		°C
Тотн	OTP Hysteresis		_	+30	_	°C
V _{IOVP}	V _{IN} Over Voltage Protection	-	_	6.25	_	V
V _{IHSY}	IOVP Hysteresis	_	_	0.25	_	V
tss	Soft-start Time	-	_	1.8	_	ms

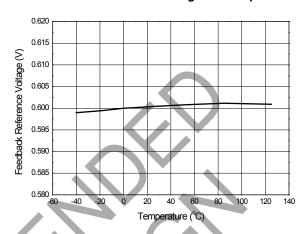


Performance Characteristics ($@T_A = +25^{\circ}C$, $V_{IN} = 5V$, $V_{OUT} = 1.8V$, unless otherwise specified.)

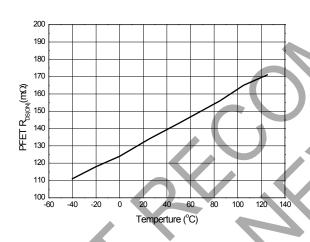
Efficiency vs. Load Current



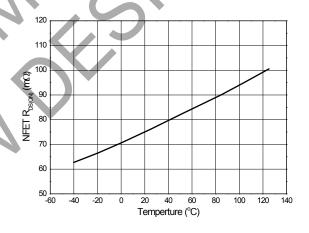
Feedback Reference Voltage vs. Temperature



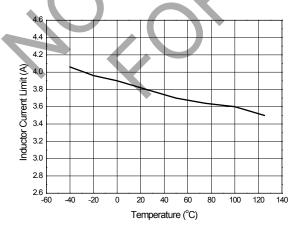
PFET Drain-Source On-State Resistance vs. Temperature



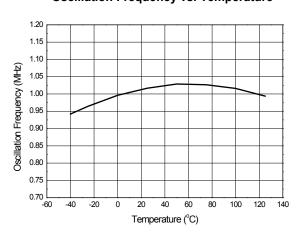
NFET Drain-Source On-State Resistance vs. Temperature



Inductor Current Limit vs. Temperature



Oscillation Frequency vs. Temperature





Performance Characteristics (Cont. @T_A = +25°C, V_{IN} = 5V, V_{OUT} = 1.8V, unless otherwise specified.)





Application Information

Typical application circuit is shown in the application circuit and for the circuit parameters setting please refers to the following descriptions.

Under Voltage Lockout (UVLO) Circuit

The AP3429/A provides an under voltage lockout circuit to prevent it from undefined status. When the V_{IN} drops lower than the UVLO detector threshold, the UVLO circuit starts to operate, V_{REF} stops, and high-side and low-side built-in switch transistors turn "OFF". As a result, V_{OUT} drops according to the COUT capacitance value and the load. When the V_{IN} is rising higher than UVLO released voltage, the IC will restart the operation.

Over Current Protection

The AP3429/A has internal over current protection function to protect from catastrophic failures. The IC can monitor the PMOS current, if the peak current is higher than the current limit threshold, OCP function will be triggered and enter cycle by cycle current limit mode. If V_{FB} drops under 0.3V for example, output node shorted to GND, AP3429 will enter latch off mode. IC will turn off both power switches. It will remain latch off state until the V_{IN} or Enable recycled to release it. AP3429A will enter hiccup mode to protect itself, if short circuit is removed, and V_{FB} rises over 0.3V, the AP3429A recovers to normal operation again.

Over Voltage Protection

The AP3429 has internal output OVP circuits. When V_{OUT} is exceeds 120% of the regulation level for more than 40 μ s, the power switching will be turned off. IC enter latch off mode and will restart until V_{IN} or Enable voltage recycled.

Over Temperature Protection

The internal thermal temperature protection circuitry of AP3429/A is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When the junction temperature exceeds +160°C, it shuts down the internal control circuit and switching power MOSFET. The AP3429/A will restart automatically under the control of soft start circuit when the junction temperature decreases to +130°C.

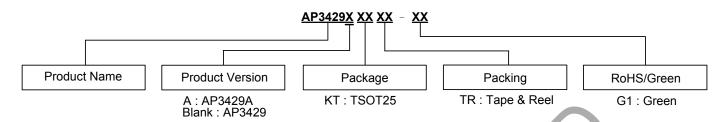
Input Over Voltage Protection

When input voltage of AP3429/A is near 6.25V, the IC will enter Input-Over-Voltage-Protection. It would be shut down and there will be no output voltage in this state. As the input voltage goes down below 6V, it will leave input OVP and recover the output voltage.



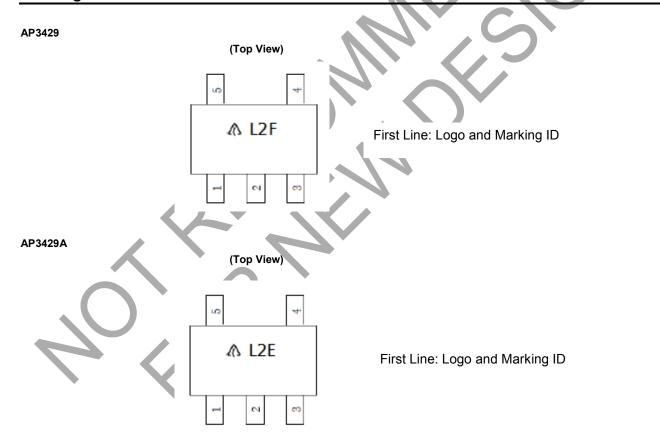


Ordering Information



Package	Temperature Range	Part Number	Marking ID	Packing	Status
T00T0T	AP3429AKTTR-G1	L2E	3000/Tape & Reel	NRND	
TSOT25	-40 to +85°C	AP3429KTTR-G1	L2F	3000/Tape & Reel	NRND

Marking Information

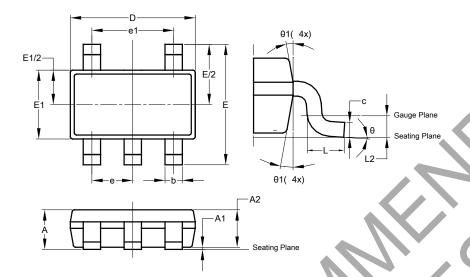




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(1) Package Type: TSOT25

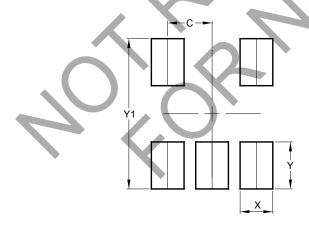


TSOT25				
Dim	Min	Max	Тур	
Α	1	1.00	-	
A1	0.01	0.10	-	
A2	0.84	0.90	-	
b	0.30	0.45	-	
С	0.12	0.20	-	
D	-	-	2.90	
E	-	·	2.80	
E1	1	•	1.60	
е	Į	0.95 BS	C	
e1	1.90 BSC			
J	0.30	0.50		
L2	0.25 BSC			
θ	0°	8°	4°	
θ1	4°	12°	-	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) Package Type: TSOT25



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3 199



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